



STSJ18NF3LL

N-CHANNEL 30V - 0.016 Ω - 18A PowerSO-8™ LOW GATE CHARGE STripFET™ II POWER MOSFET

Table 1: General Features

TYPE	V _{DSS}	R _{DS(on)}	I _D
STSJ18NF3LL	30 V	<0.019 Ω	18 A

- TYPICAL R_{DS(on)} = 0.016 Ω @ 10V
- TYPICAL Q_g = 12.5 nC @ 4.5 V
- CONDUCTION LOSSES REDUCED
- SWITCHING LOSSES REDUCED
- IMPROVED JUNCTION-CASE THERMAL RESISTANCE

DESCRIPTION

This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. This silicon, housed in thermally improved SO-8™ package, exhibits optimal on-resistance versus gate charge trade-off plus lower R_{thj-c}.

APPLICATIONS

- SPECIFICALLY DESIGNED AND OPTIMISED FOR HIGH EFFICIENCY CPU CORE DC/DC CONVERTERS FOR MOBILE PCs

Figure 1: Package

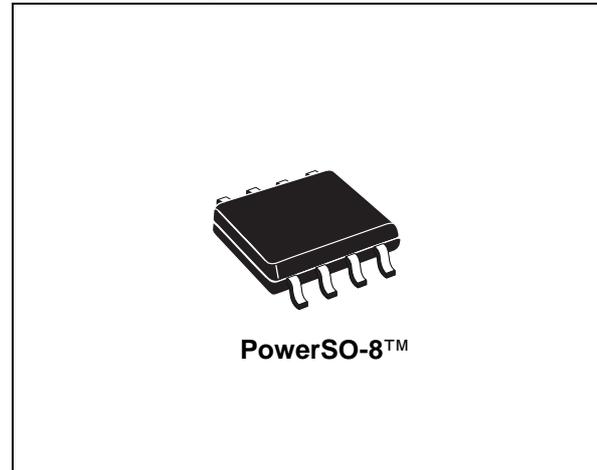


Figure 2: Internal Schematic Diagram

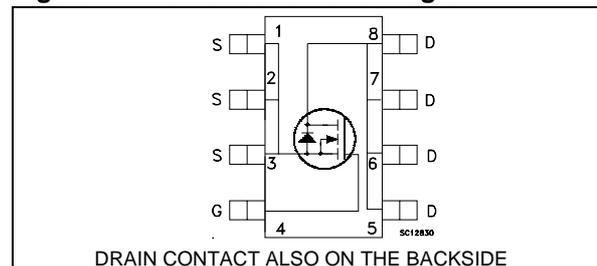


Table 2: Order Codes

SALES TYPE	MARKING	PACKAGE	PACKAGING
STSJ18NF3LL	18F3LL)	PowerSO-8	TAPE & REEL

Table 3: ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	30	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 k Ω)	30	V
V _{GS}	Gate- source Voltage	\pm 16	V
I _D	Drain Current (continuous) at T _C = 25°C (*)	18	A
I _D	Drain Current (continuous) at T _C = 100°C(*)	18	A
I _{DM} (●)	Drain Current (pulsed)	72	A
P _{tot}	Total Dissipation at T _C = 25°C	70	W
	Total Dissipation at T _C = 25°C (#)	3	W

(●) Pulse width limited by safe operating area.

(*) Value limited by wires bonding

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Table 4: THERMAL DATA

Rthj-c	Thermal Resistance Junction-case	Max	1.8	°C/W
Rthj-amb	(*)Thermal Resistance Junction-ambient	Max	41.7	°C/W
T _j	Maximum Operating Junction Temperature		150	°C
T _{stg}	Storage Temperature		-55 to 150	°C

(*) When Mounted on FR-4 board with 1 inch² pad, 2 oz of Cu and t ≤ 10 sec.

ELECTRICAL CHARACTERISTICS (T_{CASE} = 25 °C UNLESS OTHERWISE SPECIFIED)

Table 5: OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0	30			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _C = 125°C			1 10	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 16 V			±100	nA

Table 6: ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μA	1			V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V I _D = 9 A V _{GS} = 4.5 V I _D = 9 A		0.016 0.019	0.019 0.022	Ω Ω

Table 7: DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} =15 V I _D = 9 A		17		S
C _{iSS} C _{oSS} C _{rSS}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		800 250 60		pF pF pF

ELECTRICAL CHARACTERISTICS (continued)

Table 8: SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD} = 15\text{ V}$ $I_D = 9\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 4.5\text{ V}$ (Resistive Load, Figure 15)		18 32		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD}=15\text{V}$ $I_D=18\text{A}$ $V_{GS}=4.5\text{V}$ (see test circuit, Figure 16)		12.5 3.2 4.5	17	nC nC nC

Table 9: SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	$V_{DD} = 15\text{ V}$ $I_D = 9\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 4.5\text{ V}$ (Resistive Load, Figure 17)		21 11		ns ns

Table 10: SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM} (\bullet)$	Source-drain Current Source-drain Current (pulsed)				18 72	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 18\text{ A}$ $V_{GS} = 0$			1.2	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 18\text{ A}$ $di/dt = 100\text{A}/\mu\text{s}$ $V_{DD} = 15\text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, Figure 17)		23 17 1.5		ns nC A

(\bullet) Pulse width limited by safe operating area.
 (*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

Figure 3: Safe Operating Area

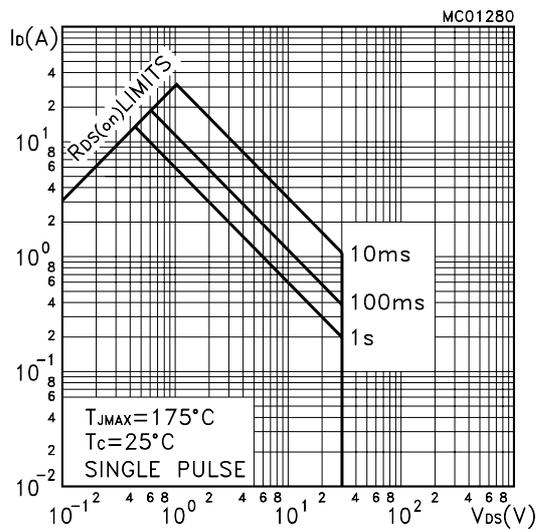


Figure 4: Thermal Impedance

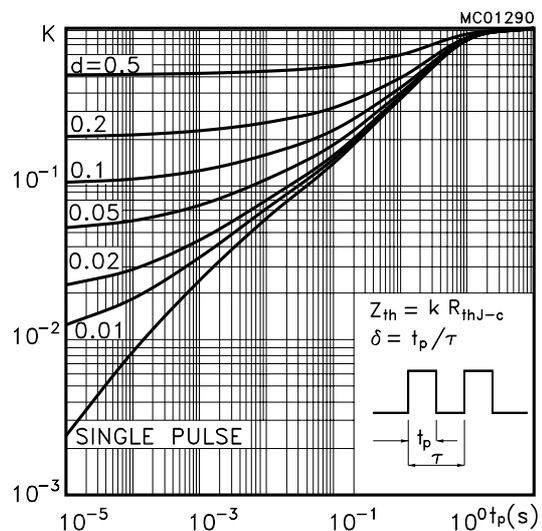


Figure 5: Output Characteristics

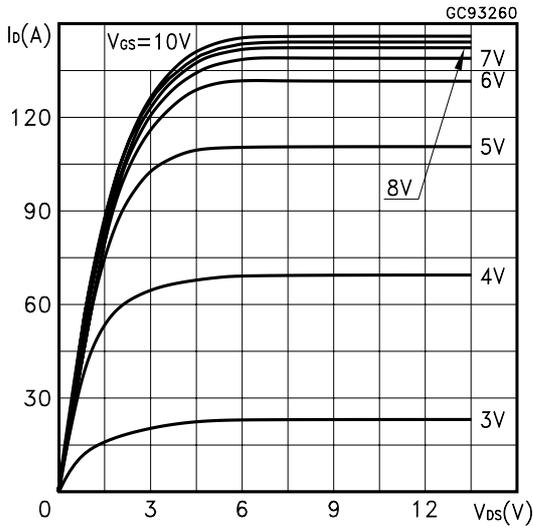


Figure 7: Transconductance

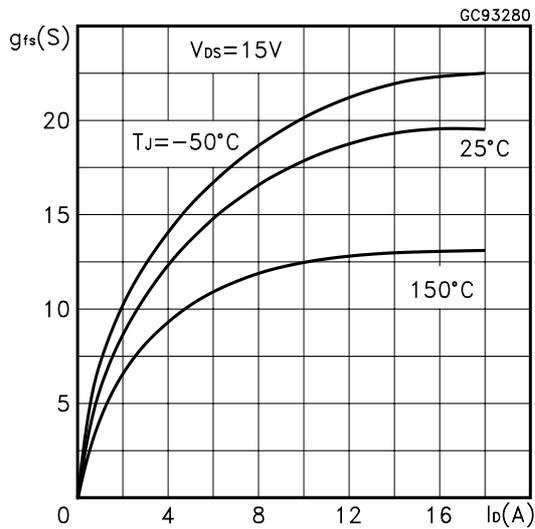


Figure 9: Gate Charge vs Gate-source Voltage

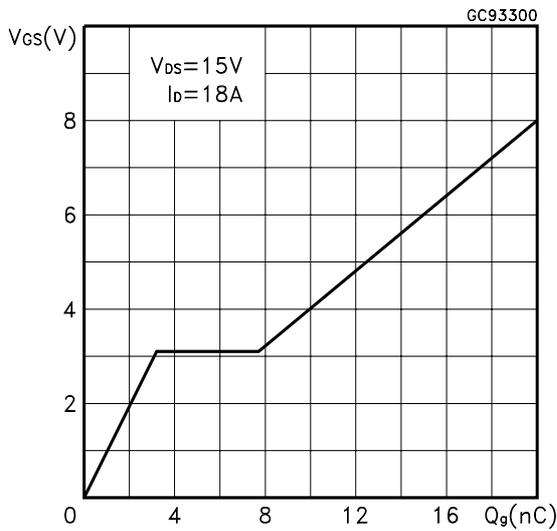


Figure 6: Transfer Characteristics

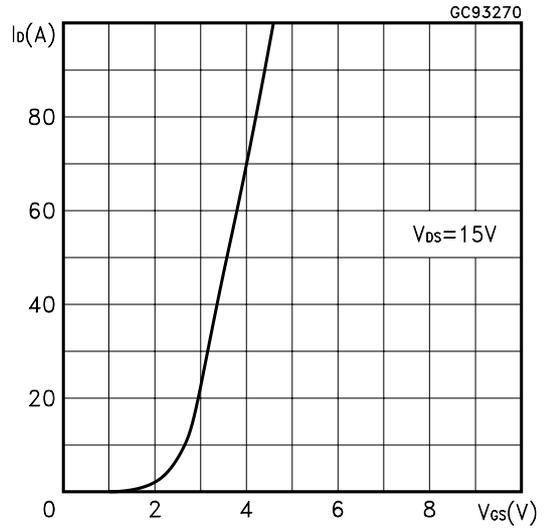


Figure 8: Static Drain-source On Resistance

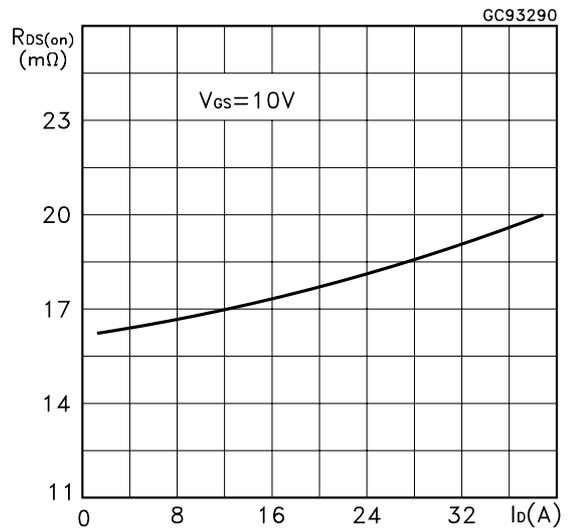


Figure 10: Capacitance Variations

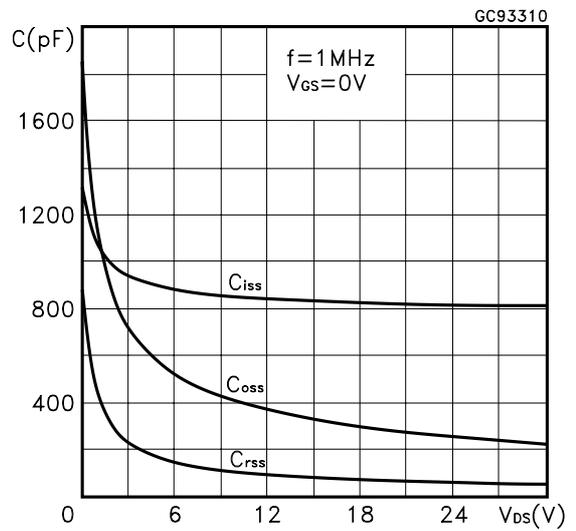


Figure 11: Normalized Gate Threshold Voltage vs Temperature

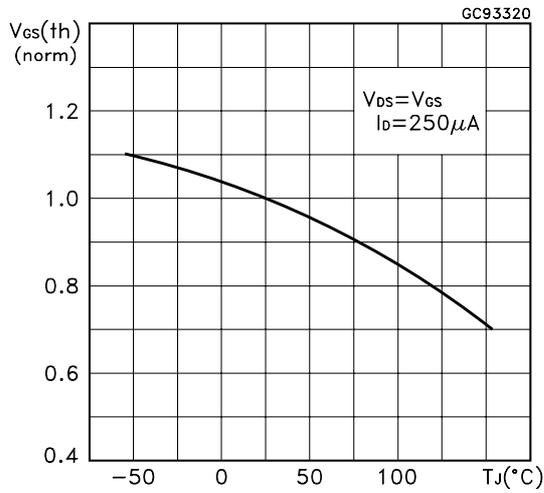


Figure 12: Normalized on Resistance vs Temperature

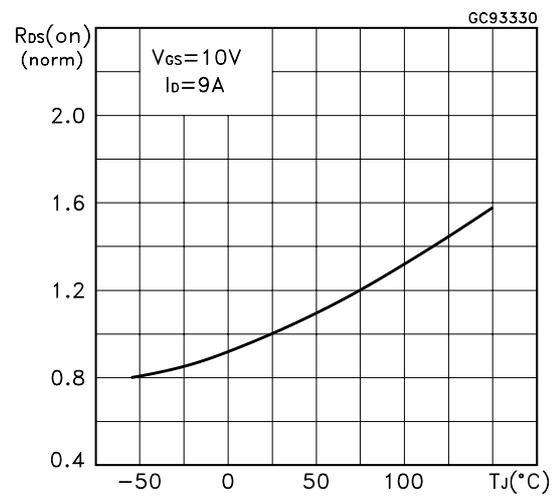


Figure 13: Source-drain Diode Forward Characteristics

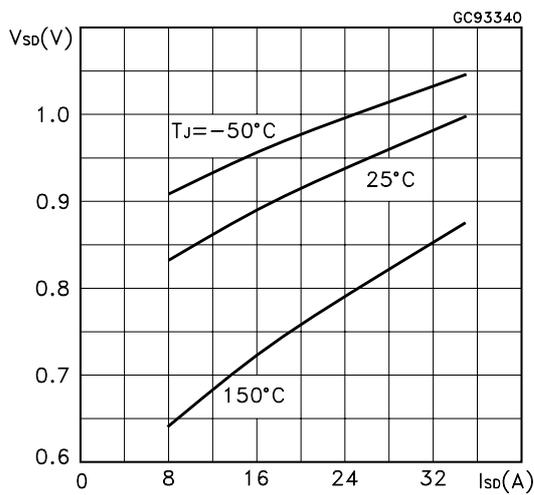


Figure 14: Normalized Breakdown Voltage vs Temperature.

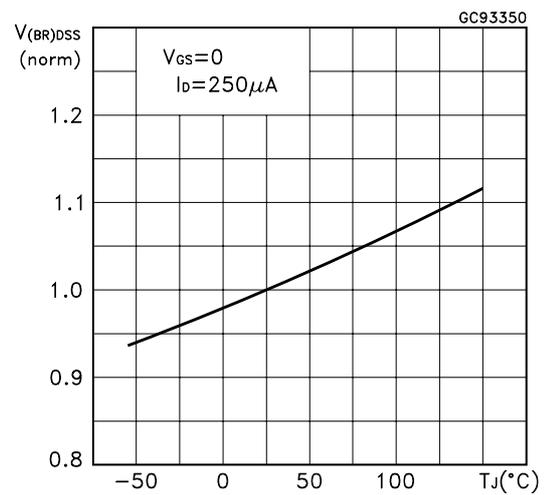


Fig. 15 Switching Times Test Circuits For Resistive Load

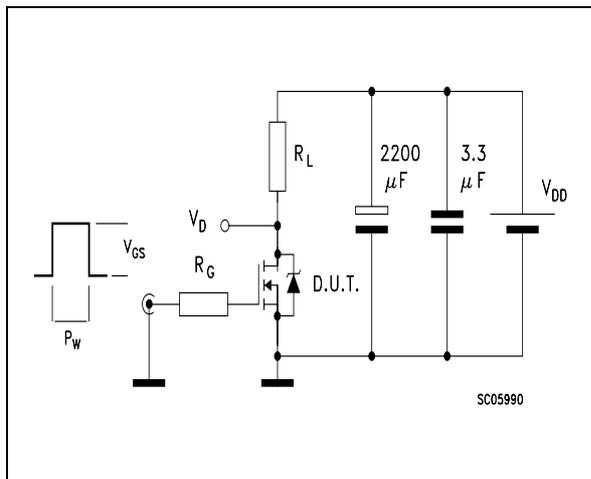


Fig.16: Gate Charge test Circuit

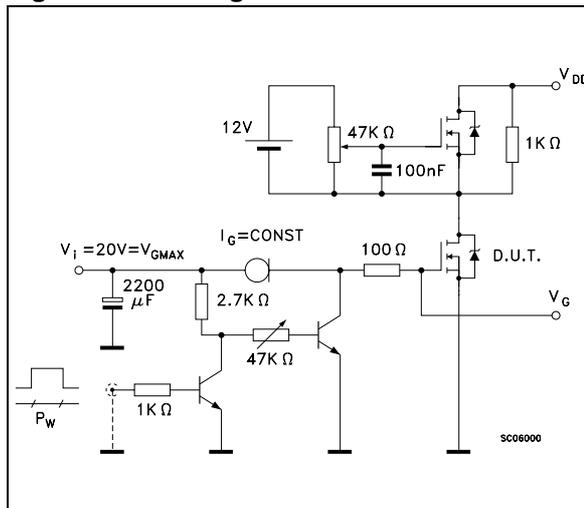
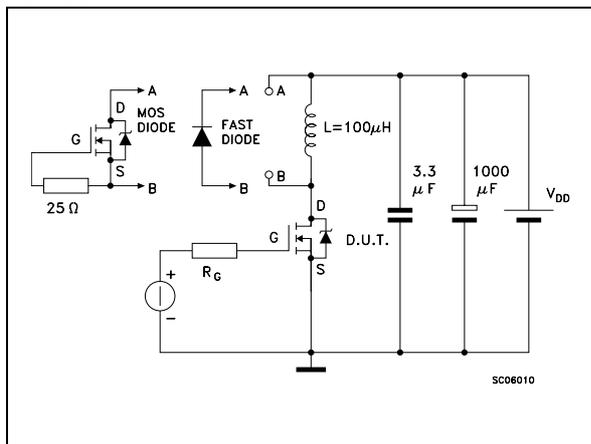


Fig. 17: Test Circuit For Diode Recovery Behaviour



PowerSO-8™ MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.019
c1	45° (typ.)					
D	4.8		5.0	0.188		0.196
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
e4		2.79			0.110	
F	3.8		4.0	0.14		0.157
L	0.4		1.27	0.015		0.050
M			0.6			0.023
S	8° (max.)					

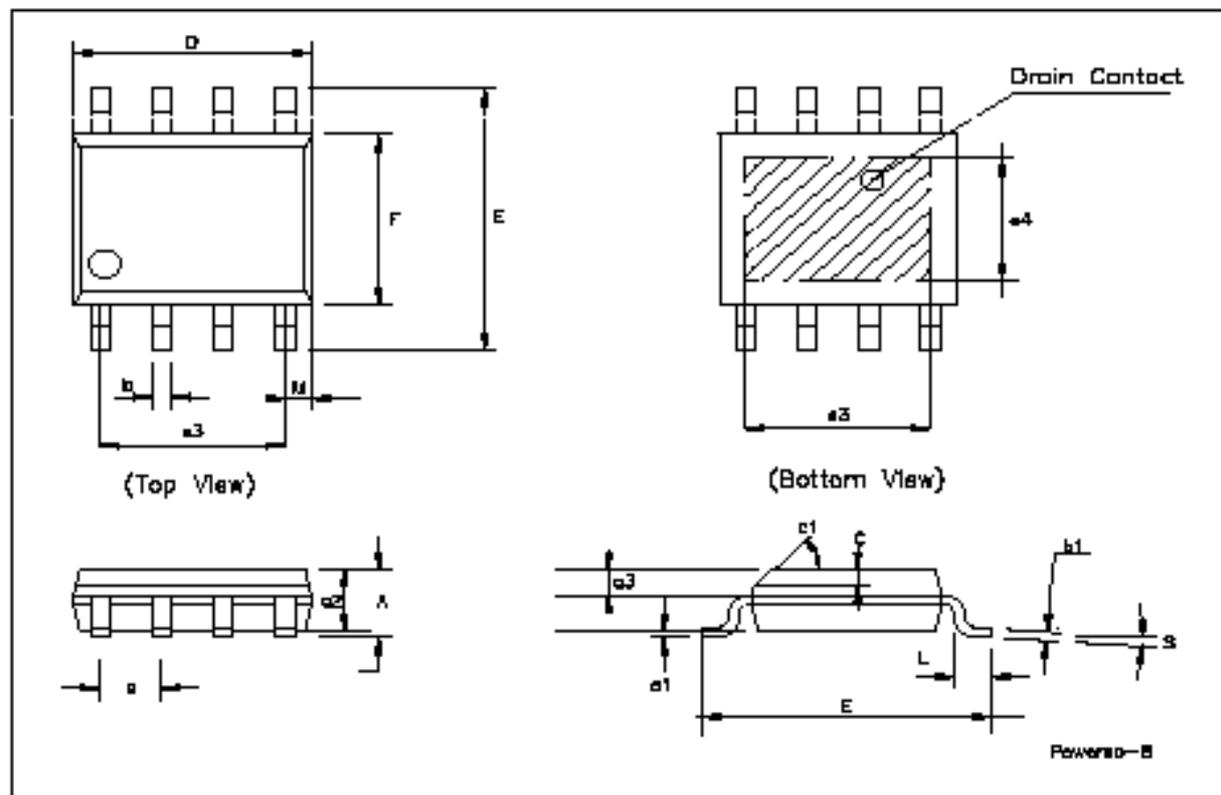


Table 11:Revision History

Date	Revision	Description of Changes
March 2005	1.0	FIRST ISSUE

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